

Docket: 740819-617
Reissue Application No. 09/986,997
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AMENDMENT TO THE CLAIMS

Please amend the claim as follows:

39. (Amended) A method for fabricating a semiconductor device, comprising the steps of:

- a) forming a semiconductor layer of a Group III nitride containing a dopant over a substrate;
- b) forming a p-side electrode out of a metal on the semiconductor layer; and
- c) after introducing the substrate into a vacuum chamber, charging plasma into the vacuum chamber to form an ambient of plasma while keeping the temperature of the substrate at about 600°C or lower, thereby making the conductivity type of the semiconductor layer p-type,
wherein the ambient of the plasma includes nitrogen plasma.